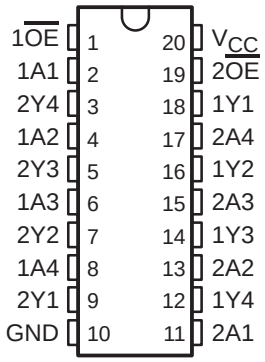
- **BiCMOS Technology With Low Quiescent Power**
- **Buffered Inputs**
- **Noninverted Outputs**
- **Input/Output Isolation From V_{CC}**
- **Controlled Output Edge Rates**
- **64-mA Output Sink Current**
- **Output Voltage Swing Limited to 3.7 V**
- **SCR Latch-Up-Resistant BiCMOS Process and Circuit Design**
- **Package Options Include Plastic Small-Outline (M) and Shrink Small-Outline (SM) Packages and Standard Plastic (E) DIP**

CD74FCT244, CD74FCT244AT . . . E, M, OR SM PACKAGE
(TOP VIEW)



description

The CD74FCT244 and CD74FCT244AT are octal buffer/line drivers with 3-state outputs using a small-geometry BiCMOS technology. The output stages are a combination of bipolar and CMOS transistors that limit the output high level to two diode drops below V_{CC}. This resultant lowering of output swing (0 V to 3.7 V) reduces the power-bus ringing [a source of electromagnetic interference (EMI)] and minimizes V_{CC} bounce and ground bounce and their effects during simultaneous output switching. The output configuration also enhances switching speed and is capable of sinking 64 mA.

These devices are organized as two 4-bit buffers/line drivers with separate active-low output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

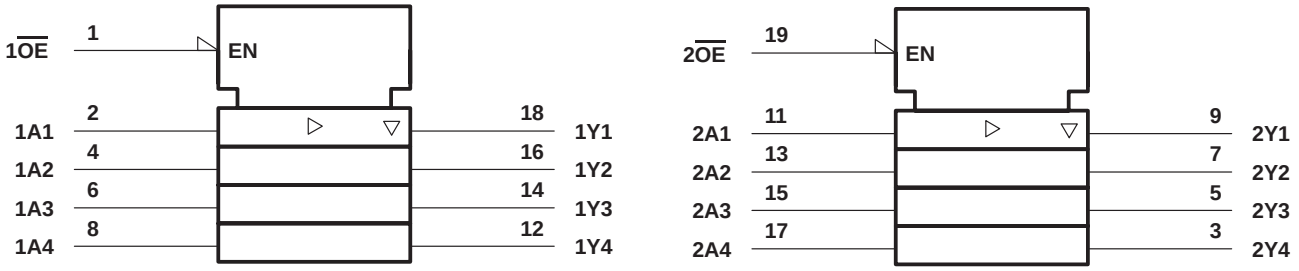
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The CD74FCT244 and CD74FCT244AT devices are characterized for operation from 0°C to 70°C.

FUNCTION TABLE
(each buffer/driver)

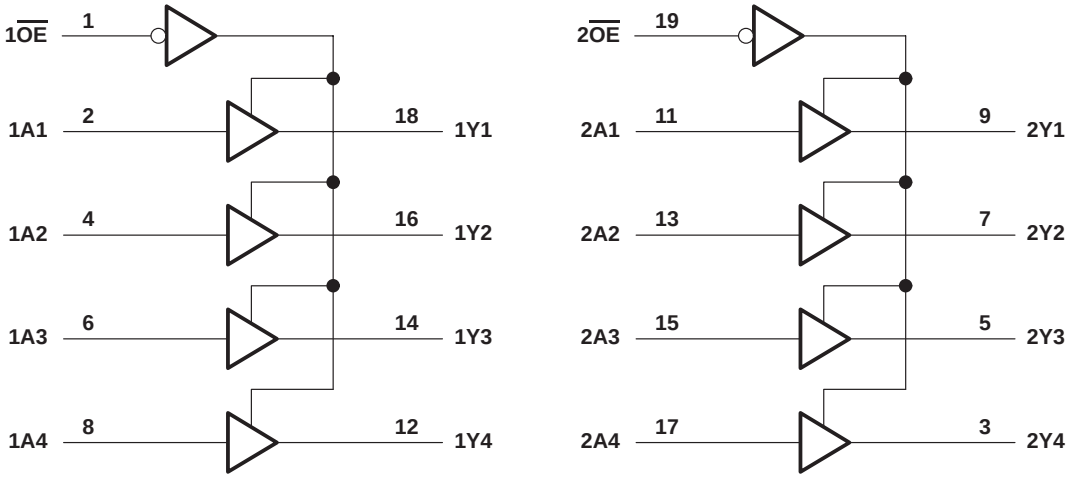
INPUTS		OUTPUT
$\overline{OE}$	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

DC supply voltage range, V_{CC} . . . . . –0.5 V to 6 V
DC input clamp current, I_{IK} (V_I < –0.5 V) . . . . . –20 mA
DC output clamp current, I_{OK} (V_O < –0.5 V) . . . . . –50 mA
DC output sink current per output pin, I_{OL} . . . . . 70 mA
DC output source current per output pin, I_{OH} . . . . . –30 mA
Continuous current through V_{CC}, I_{CC} . . . . . 140 mA
Continuous current through GND . . . . . 528 mA
Package thermal impedance, θ_{JA} (see Note 1): E package . . . . . 69°C/W
M package . . . . . 58°C/W
SM package . . . . . 70°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 2)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	4.75	5.25	V
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
V_I	Input voltage	0	V_{CC}	V
V_O	Output voltage	0	V_{CC}	V
I_{OH}	High-level output current		–15	mA
I_{OL}	Low-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate (slew rate)	0	10	ns/V
T_A	Operating free-air temperature	0	70	°C

NOTE 2: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V_{CC}	T_A = 25°C		MIN	MAX	UNIT
				MIN	MAX			
V_{IK}	I_I = –18 mA		4.75 V		–1.2		–1.2	V
V_{OH}	I_{OH} = –15 mA		4.75 V	2.4		2.4		V
V_{OL}	I_{OL} = 64 mA		4.75 V		0.55		0.55	V
I_I	$V_I = V_{CC}$ or GND		5.25 V		±0.1		±1	μA
I_{OZ}	$V_O = V_{CC}$ or GND		5.25 V		±0.5		±10	μA
I_{OS}†	$V_I = V_{CC}$ or GND,	V_O = 0	5.25 V	–60		–60		mA
I_{CC}	$V_I = V_{CC}$ or GND,	I_O = 0	5.25 V		8		80	μA
ΔI_{CC}‡	One input at 3.4 V,	Other inputs at V_{CC} or GND	5.25 V		1.6		1.6	mA
C_i	$V_I = V_{CC}$ or GND				10		10	pF
C_o	$V_O = V_{CC}$ or GND				15		15	pF

† Not more than one output should be tested at a time, and the duration of the test should not exceed 100 ms.
‡ This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.25 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	CD74FCT244			CD74FCT244AT			UNIT
			T_A = 25°C	MIN	MAX	T_A = 25°C	MIN	MAX	
			TYP			TYP			
t_{pd}	A	Y	4.5	1.5	6.5	3.8	1.5	5.3	ns
t_{en}	$\overline{OE}$	Y	6	1.5	8	4.8	1.5	6.5	ns
t_{dis}	$\overline{OE}$	Y	5	1.5	7	4.5	1.5	5.8	ns

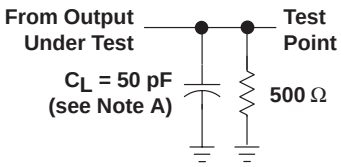
noise characteristics, V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C

PARAMETER		MIN	TYP	MAX	UNIT
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		1		V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		0.5		V
$V_{IH(D)}$	High-level dynamic input voltage	2			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.8	V

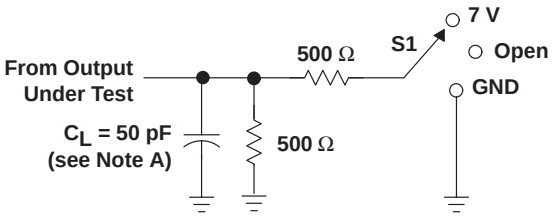
operating characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	No load, f = 1 MHz	35	pF

PARAMETER MEASUREMENT INFORMATION

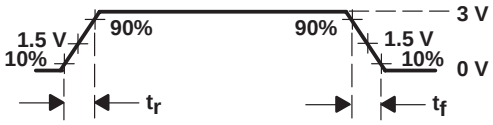


LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

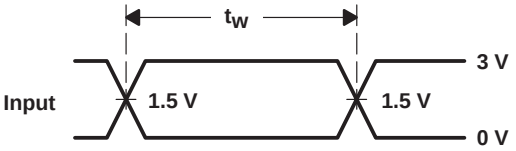


LOAD CIRCUIT FOR
3-STATE AND OPEN-DRAIN OUTPUTS

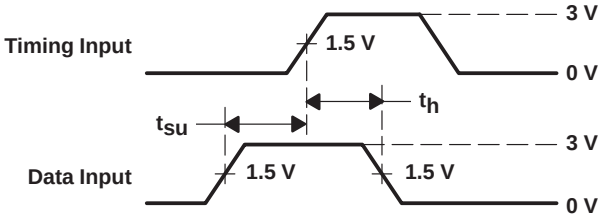
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open
Open Drain	7 V



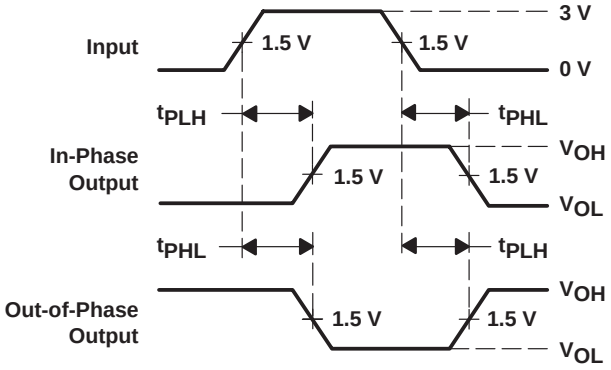
VOLTAGE WAVEFORM
INPUT RISE AND FALL TIMES



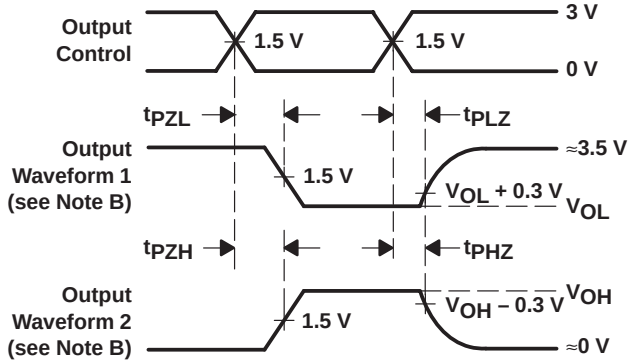
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r and t_f = 2.5 ns.
D. The outputs are measured one at a time with one input transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgment, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Customers are responsible for their applications using TI components.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.